

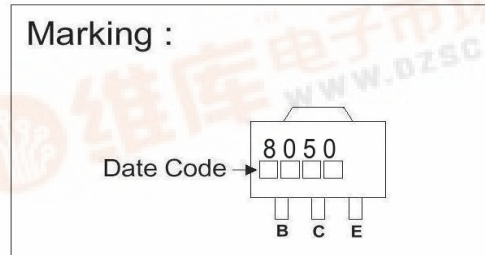
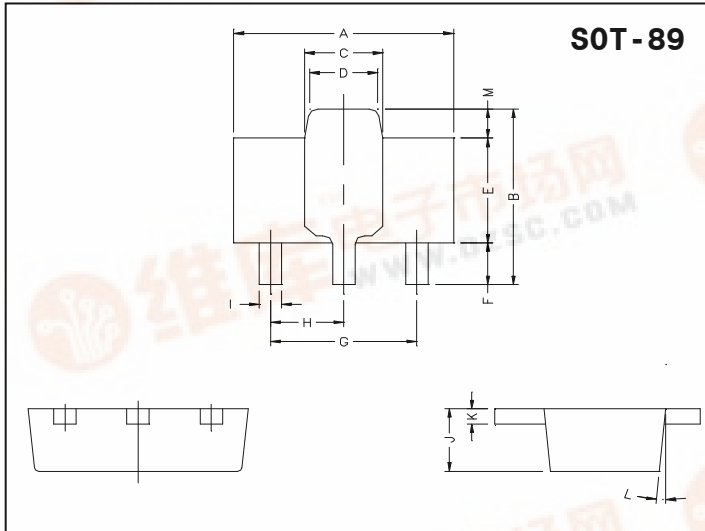
GTM CORPORATION

GM8050 NPN EPITAXIAL TRANSISTOR

Description

The GM8050 is designed for general purpose amplifier applications.

Package Dimensions



	Millimeter			Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	40	V
Collector to Emitter Voltage	VCEO	25	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	IC	1.5	A
IB Base Current	IB	0.5	A
Total Power Dissipation	PD	1	W

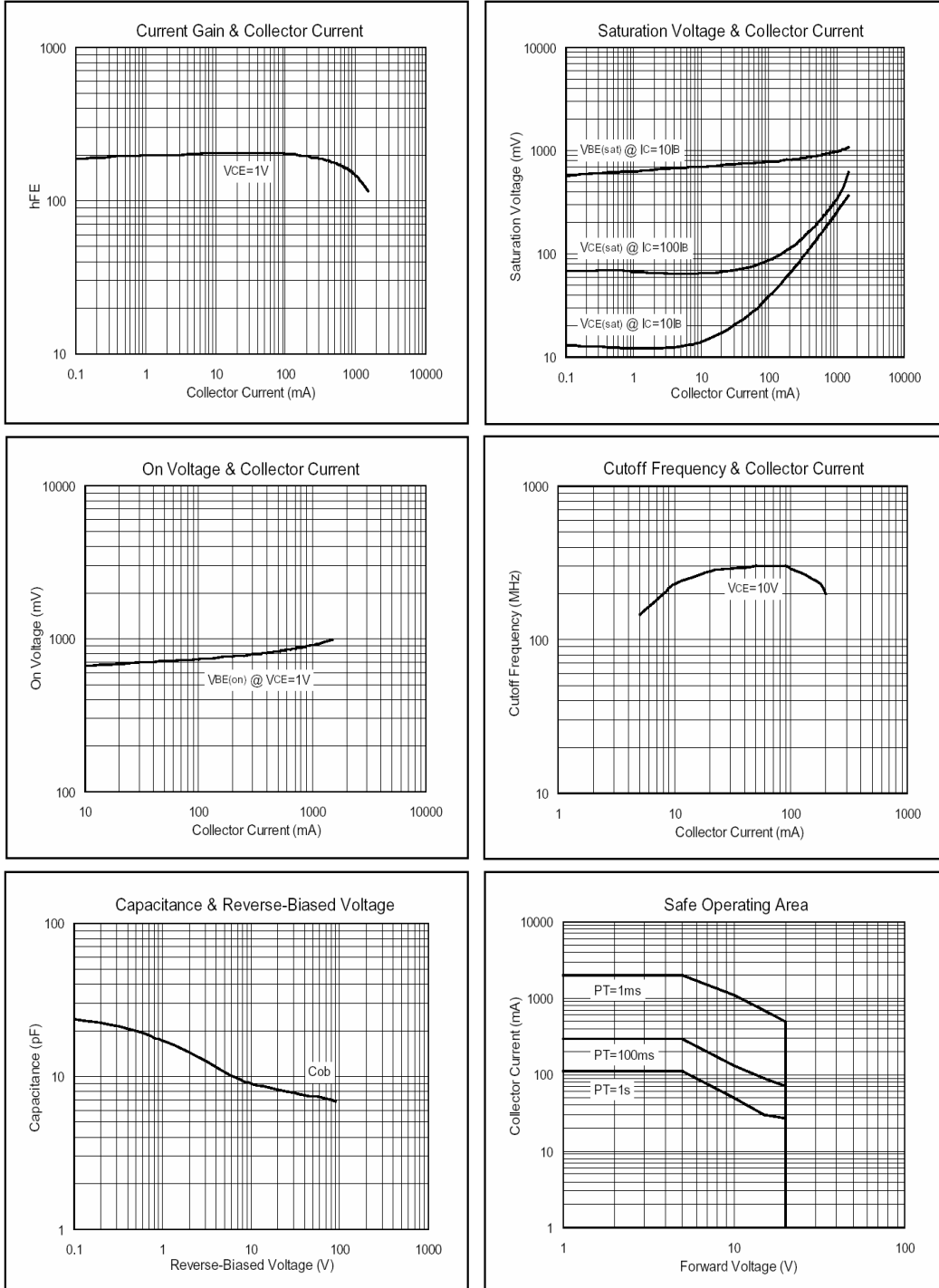
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	40	-	-	V	IC=100uA
BVCEO	25	-	-	V	IC=2mA
BVEBO	6	-	-	V	IE=100uA
ICBO	-	-	100	nA	VCB=35V
IEBO	-	-	100	nA	VEB=6V
VCE(sat)	-	-	0.5	V	IC=0.8A, IB=80mA
VBE(sat)	-	-	1.2	V	IC=0.8A, IB=80mA
VBE(on)	-	-	1	V	VCE=1V, IC=10mA
Hfe1	45	-	-		VCE=1V, IC=5mA
Hfe2	120	-	500		VCE=1V, IC=100mA
Hfe3	40	-	-		VCE=1V, IC=800mA
fT	100	-	-	MHz	VCE=10V, IC=50mA

Classification Of hFE

Rank	C	D	E
hFE	120-200	160 - 300	250 - 500

Characteristics Curve



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